

U.S. Department of Commerce, Patent and Trademark		Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		SNDK.256US0	10/052,924
		Applicant(s)	
QTP (Use several sheets if necessary)		Mokhlesi et al.	
		Filing Date	Group
		January 18, 2002	2818

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U.S. Patent Documents

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
HJK	1 4,630,086	12/16/86	Sato et al.			
	2 5,172,338	12/15/92	Mehrotra et al.			
	3 5,172,338	7/8/97	Mehrotra et al.			
	4 5,418,752	5/23/95	Harari et al.			
	5 5,712,180	1/27/98	Guterman et al.			
	6 5,768,192	6/16/98	Eitan			
	7 5,892,706	4/6/99	Shimizu et al.			
	8 6,044,109	3/28/00	Cernea et al.			
	9 6,103,573	8/15/00	Harari et al.			
HJK	10 6,222,762	4/24/01	Guterman et al.			

U.S. Published Patent Application Documents

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

Foreign Patent Documents

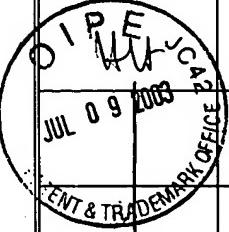
Translation

	Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

HJK	11	Bauza et al., "In-Depth Exploration of Si-SiO ₂ Interface Traps in MOS Transistors Using the Charge Pumping Technique," <i>IEEE Transactions on Electron Devices</i> , Vol. 44, No. 12, December 1997, pp. 2262-2266.
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	27	Pohm, A.V., et al., "The Design of a One Megabit Non-Volatile M-R Memory Chip Using 1.5*5 mu m Cells," <i>IEEE Transactions on Magnetics</i> , Vol. 24, No. 6, November 1988, pp. 3117-3119.
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Examiner Huan Hoang

Date Considered

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.